

The spin-double refraction in two-dimensional electron gas

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Abstract

We briefly review the phenomenon of the spin-double refraction that originates at an interface separating a two-dimensional electron gas with Rashba spin-orbit coupling from a one without. We demonstrate how this phenomenon in semiconductor heterostructures can produce and control a spin-polarized current without ferromagnetic leads.

Key words: Rashba effect, spin-FET

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Spintronics is a multidisciplinary field whose central subject is the active control and manipulation of spin degrees of freedom in solid-state systems [1,2]. The attempts to realize the spin Field-Effect Transistor (spin-FET) proposed by Datta and Das [3], based on Rashba Spin-Orbit (SO) coupling [4], have been unsuccessful because of the difficulty of inject spin-polarized carriers from a ferromagnetic metal into a semiconductor [5]. One of the way to solve the problem of the conductivity mismatch at the ferromagnet-semiconductor interface is to use dilute magnetic semiconductor as input source [6].

We have proposed [7] an alternative way to overcome the problem of the conductivity mismatch. In this work we consider the phenomenon of the spin-double refraction. A similar effect has been successively presented by Khodas *et al.* [8]. This is observed in two-Dimensional Electron Gas (2DEG) when electrons are injected with an angle out of the normal on an interface separating a region without Rashba SO coupling (NR zone) from a region with

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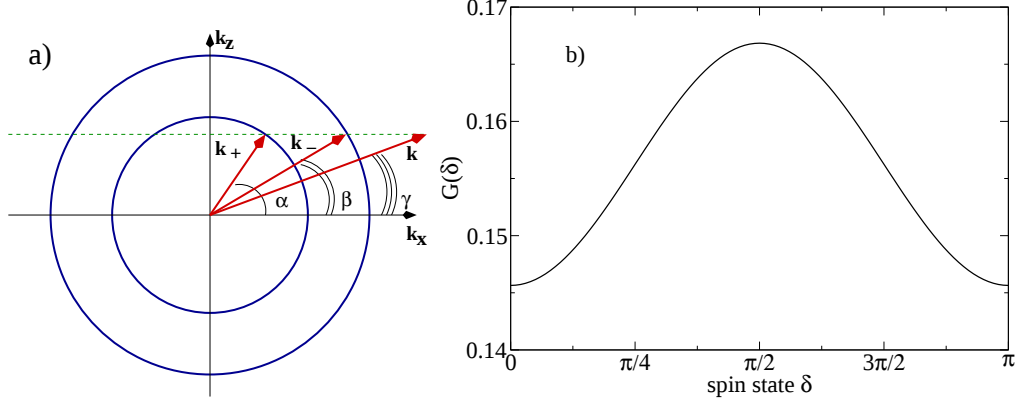


Fig. 1. Panel a): the vectors $\vec{k}_+$, $\vec{k}_-$ and $\vec{k}$ in k -space and the angles α , β and γ that they form with x direction normal to the interface. The two circles are the Fermi contour at a fixed energy. Panel b): the conductance for polarized electrons $\mathcal{G}$ as a function of the spin polarization δ of the incoming electrons. The value $\delta = 0$ corresponds to spin up and $\delta = \pi/2$ to spin down.

it (R zone). The behavior of electron spin in such scattering is analogous to the polarization of the light in a biaxial crystal: the incident ray splits, within the crystal, in two rays (ordinary and extraordinary) whose polarizations are orthogonal.

The Hamiltonian describing the hybrid system is

$$\mathcal{H}_{\text{NR-R}} = \vec{p} \frac{1}{2m(x)} \vec{p} + \frac{k_{\text{SO}}(x)m(x)}{\hbar^2} (\sigma_z p_x - \sigma_x p_z) - i\sigma_z \frac{1}{2} \frac{\partial k_{\text{SO}}(x)}{\partial x} + U\delta(x). \quad (1)$$

The second term is the Rashba SO coupling. The presence of the interface is introduced by the mass and the strength of SO coupling that are piecewise constant

$$\frac{1}{m}(x) = \frac{\vartheta(-x)}{m_{\text{NR}}} + \frac{\vartheta(x)}{m_{\text{R}}} \quad \text{and} \quad k_{\text{SO}}(x) = k_{\text{SO}} \vartheta(x), \quad (2)$$

where $\vartheta(x)$ is the step function. The third term in (1) is needed to get an hermitian operator $\mathcal{H}_{\text{NR-R}}$ and the fourth term regulates the transparency of the interface. Let us consider an electron injected from the NR zone on the interface with momentum k and angle γ . The electron wave function in the R zone is given by the superposition of the split eigenstates of the R zone, whose directions are fixed by the conservation of the momentum parallel to the interface

$$k_+ \sin \alpha = k_- \sin \beta = k \sin \gamma \quad (3)$$

where $k_{\pm} = \sqrt{\mu k^2 + k_{\text{SO}}^2} \mp k_{\text{SO}}$ is the momentum relative to the two eigenstates (see Fig. 1 Panel a) and $\mu = m_{\text{N}}/m_{\text{NR}}$. The two eigenstates of the R zone are characterized by two limit angles

$$\gamma_0 = \arcsin \frac{k_+}{k} \quad \text{and} \quad \gamma_1 = \arcsin \frac{k_-}{k} > \gamma_0 \quad (4)$$

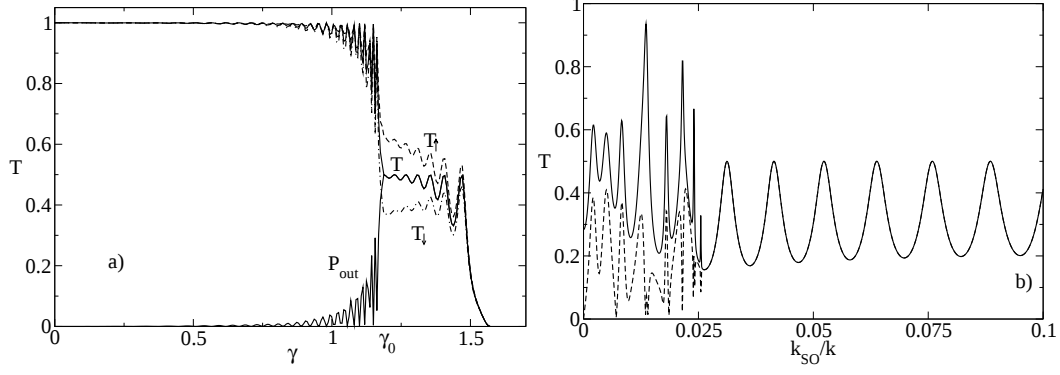


Fig. 3. Panel a): The transmission coefficients $T_{\downarrow}(\gamma)$, $T(\gamma)$, $T_{\uparrow}(\gamma)$ as functions of the incidence angle γ (in radians). Panel b): The transmission coefficient for unpolarized electrons when $\gamma = 1.25$. The threshold $\bar{k}_{SO}$ is $0.025k$. The dotted curve gives the output spin polarization, the length of the Rashba zone is $L = 283$ nm.

k_{SO} with a gate. We stress that a modulation of the output current can be obtained with a spin-unpolarized input current, whereas in the original Datta and Das [3] proposal the current oscillation stems out from the difference of phase accumulated along a path in the Rashba region by the two spin propagating modes. In our system the current modulation and the spin polarization appear when *only one mode* propagates through the Rashba barrier.

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